

2SC1360, 2SC1360A

Silicon NPN epitaxial planar type

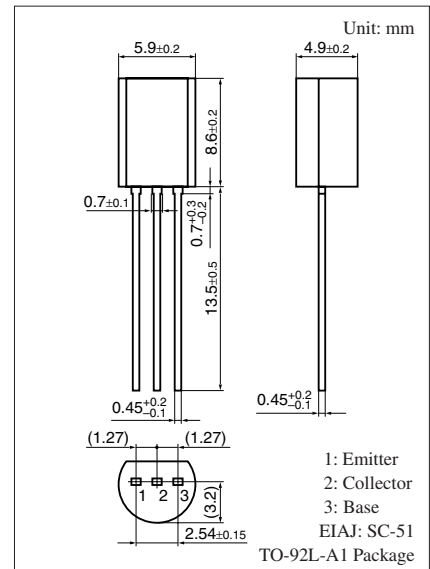
For intermediate frequency amplification of TV image

■ Features

- High transition frequency f_T
- Large collector power dissipation P_C

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

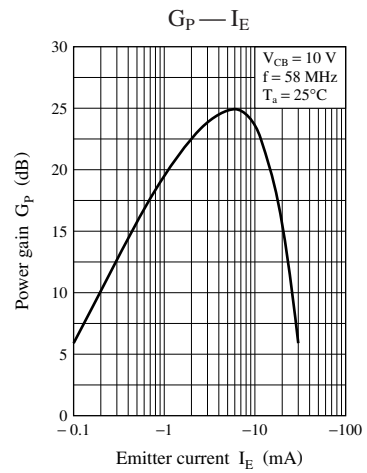
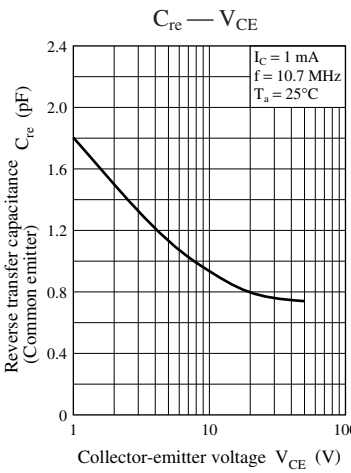
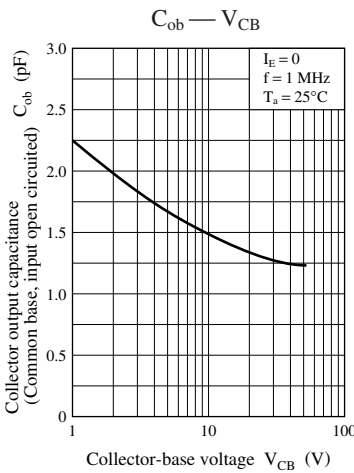
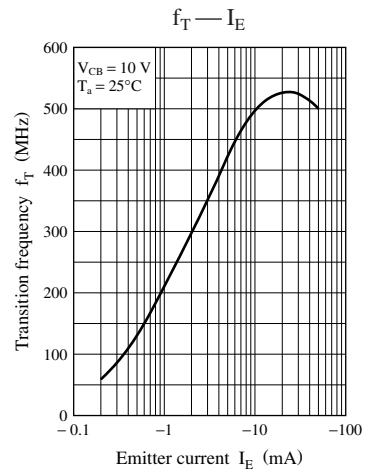
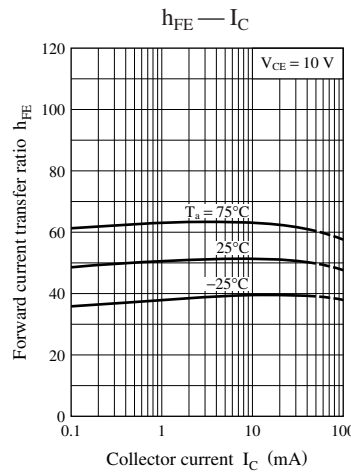
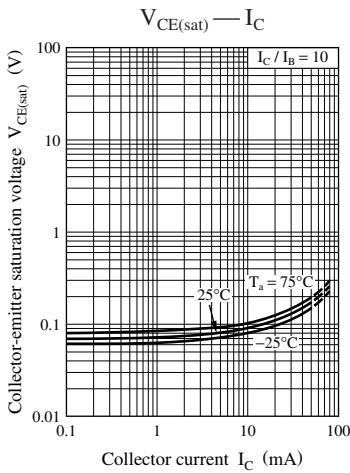
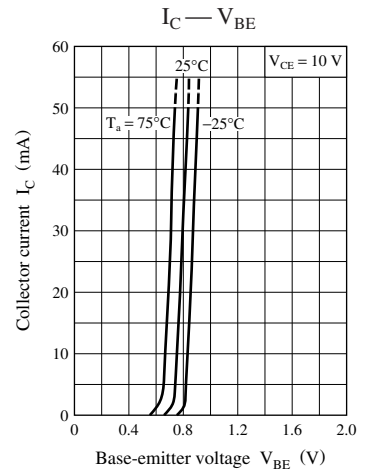
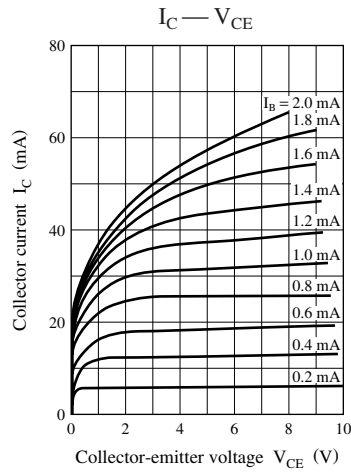
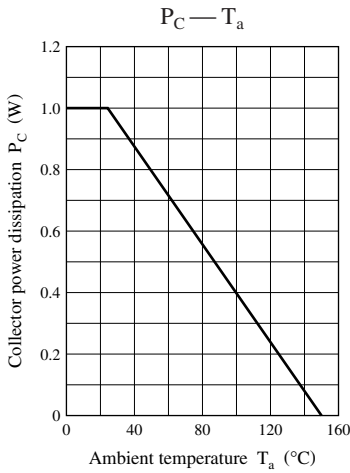
Parameter	Symbol	Rating	Unit
Collector-base voltage (Emitter open)	2SC1360	50	V
	2SC1360A	60	
Collector-emitter voltage (Base open)	2SC1360	45	V
	2SC1360A	60	
Emitter-base voltage (Collector open)	V_{EBO}	4	V
Collector current	I_C	50	mA
Collector power dissipation	P_C	1	W
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$



■ Electrical Characteristics $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Collector-base voltage (Emitter open)	2SC1360	$I_C = 100 \mu\text{A}, I_E = 0$	50			V
	2SC1360A					
Collector-emitter voltage (Base open)	2SC1360	$I_C = 3 \text{ mA}, I_B = 0$ $I_C = 1 \text{ mA}, I_B = 0$	45			V
	2SC1360A					
Emitter-base voltage (Collector open)	V_{EBO}	$I_E = 100 \mu\text{A}, I_C = 0$	4			V
Collector-base cutoff current (Emitter open)	I_{CBO}	$V_{CB} = 20 \text{ V}, I_E = 0$			100	nA
Forward current transfer ratio	h_{FE}	$V_{CE} = 10 \text{ V}, I_C = 10 \text{ mA}$	20	50	100	—
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 20 \text{ mA}, I_B = 2 \text{ mA}$			0.4	V
Transition frequency	2SC1360	$V_{CB} = 10 \text{ V}, I_E = -10 \text{ mA}, f = 100 \text{ MHz}$	300	500		MHz
	2SC1360A					
Reverse transfer capacitance (Common emitter)	2SC1360	$V_{CB} = 10 \text{ V}, I_E = -1 \text{ mA}, f = 10.7 \text{ MHz}$		0.96	1.5	pF
	2SC1360A					
Power gain	2SC1360	$V_{CB} = 10 \text{ V}, I_E = -10 \text{ mA}, f = 58 \text{ MHz}$	22	26	30	dB
	2SC1360A					

Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.



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